Reply to Office Action of October 21, 2009

IN THE SPECIFICATION

Please replace the Abstract with the Substitute Abstract attached hereto.

Please amend the paragraph beginning at page 8, line 8, as follows:

The results obtained on standard layers of Ni (in other words deposited continuously) are given in table II below.

Table I: Distribution parameters for particles obtained according to the invention

Ni thickness	2 nm	3 nm	5 nm	10 nm
Average	16 nm	17 nm	37.6	86.6
Standard deviation	0.7	0.7	0.5	0.6

Table I:

Distribution parameters for particles obtained according to the invention

Table II: Distribution parameters for particles obtained with standard Ni layers

Ni thickness	3 nm	10 nm
Average	54 nm	139 nm
Standard deviation	0.45	0.68

Table II:

Distribution parameters for particles obtained with standard Ni layers

Please amend the paragraph beginning at page 9, line 15, as follows:

Table III shows the result of treatment by hydrogen plasma at 300°C on a film deposited using the process according to the invention (in other words discontinuously) and using a standard process (in other words continuously).

Table III

Ni thickness	3 nm	3 nm	10 nm
Average	18 nm	No putting in	No putting in

		drops	drops
Standard deviation	0.5		
Ni deposition process	According to the invention	Standard	Standard

Table III

Please amend the paragraph beginning at page 10, line 11, as follows:

The layer 14 of Ni is made by an electron gun at ambient temperature using the device described above. An oxygen partial pressure equal to 3×10^{-5} mbars is added during the deposition of Ni.

Please amend the paragraph beginning at page 10, line 17, as follows:

Table IV contains results related to the size of catalyst particles when an oxygen partial pressure is introduced during deposition.

Table IV

Ni thickness	3 nm	3 nm	10 nm	10 nm
O ₂ partial pressure	0	3 x 10 ⁻⁵ mbars	0	3 x 10 ⁻⁵ mbars
Average	18 nm	13.5 nm	No putting in drops	24 nm
Standard deviation	0.5	0.5		0.5

Table IV